



SHENZHEN LONG JING MICRO-ELECTRONICS CO., LTD.

SOD-123 Plastic-Encapsulate Diodes

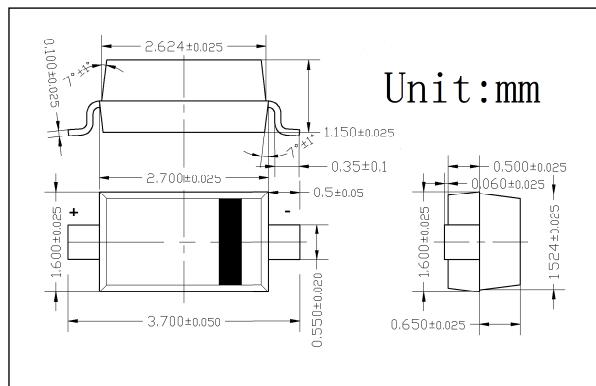
BAT54W

Features

- Low forward voltage

Applications

- Ultra high-speed switching
- Voltage clamping
- Protection circuits



Marking: B4

Maximum Ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RRM}	Peak repetitive reverse voltage	30	V
V_R	Reverse Voltage	30	V
I_F	Forward Current	200	mA
I_{FRM}	Repetitive Peak Forward Current	300	mA
I_{FSM}	Peak Forward Surge Current ($t_p = 10 \text{ ms}$)	600	mA
P_{tot}	Total Power Dissipation	200	mW
R_{thJA}	Thermal Resistance from Junction Ambient	625	K/W
T_J	Junction Temperature	125	$^\circ\text{C}$
T_s	Storage Temperature Range	- 65 to + 150	$^\circ\text{C}$

Electrical Characteristics($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Max	Unit
V_F	Forward Voltage	$I_F = 0.1 \text{ mA}$		240	mV
		$I_F = 1 \text{ mA}$		320	
		$I_F = 10 \text{ mA}$		400	
		$I_F = 30 \text{ mA}$		500	
		$I_F = 100 \text{ mA}$		1000	
$V_{(BR)R}$	Reverse Breakdown Voltage	$I_R = 100 \mu\text{A}$	30		V
I_R	Reverse Current	$V_R = 25 \text{ V}$		2	μA
C_T	Total Capacitance	$V_R = 1 \text{ V}, f = 1 \text{ MHz}$		10	pF
t_{rr}	Reverse Recovery Time	$I_F = 10 \text{ mA} \text{ through } I_R = 10 \text{ mA} \text{ to } I_R = 1 \text{ mA}, R_L = 100 \Omega$		5	ns

Typical Characteristics

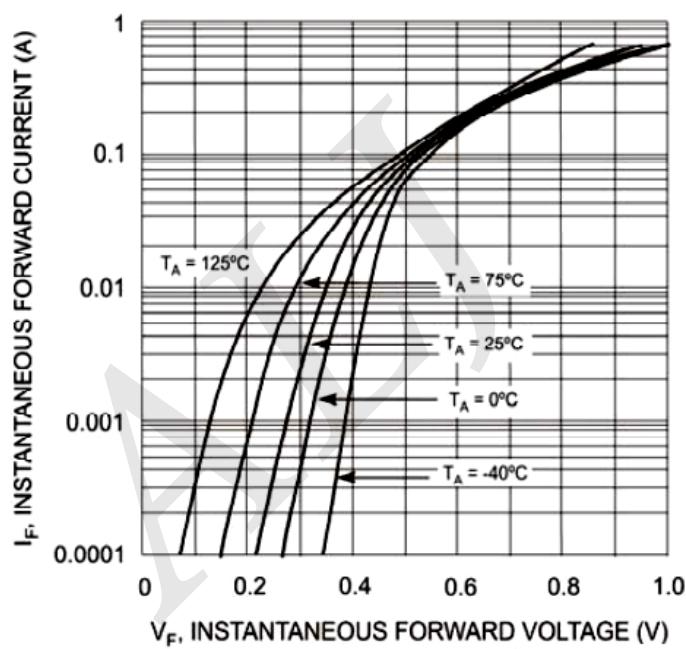


Fig. 1 Forward Characteristics

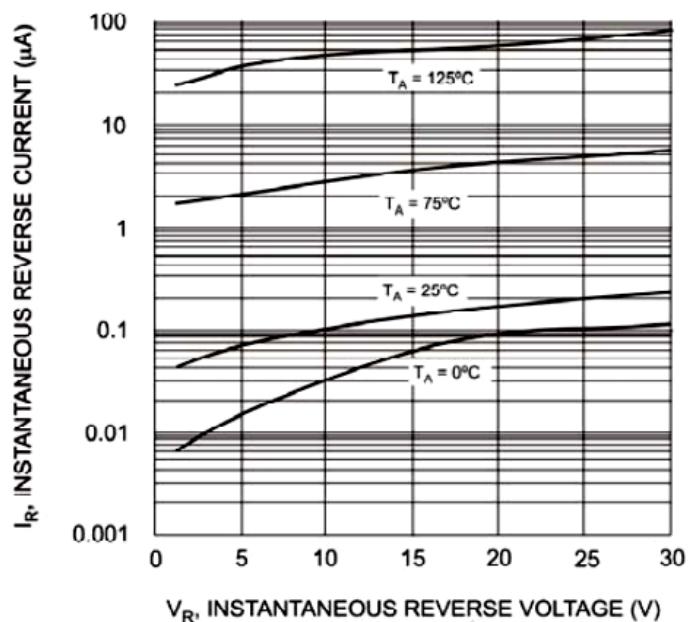


Fig. 2 Typical Reverse Characteristics

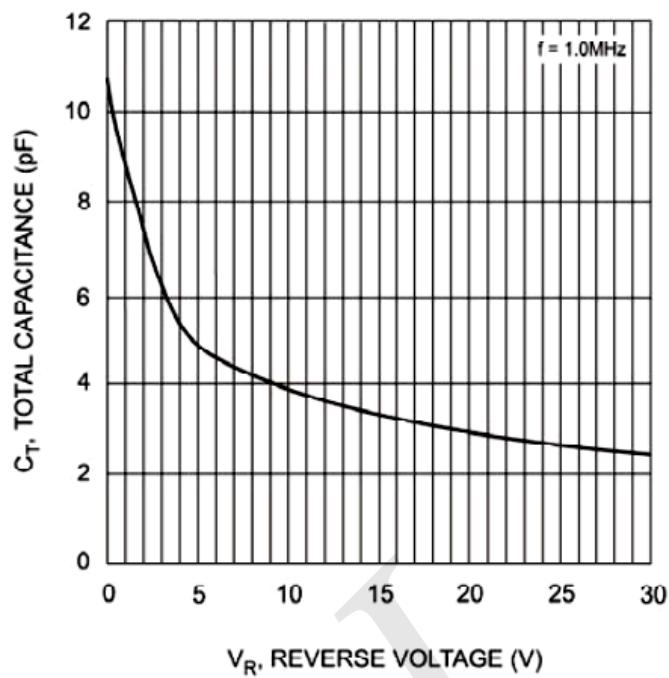


Fig. 3 Typical Capacitance vs. Reverse Voltage

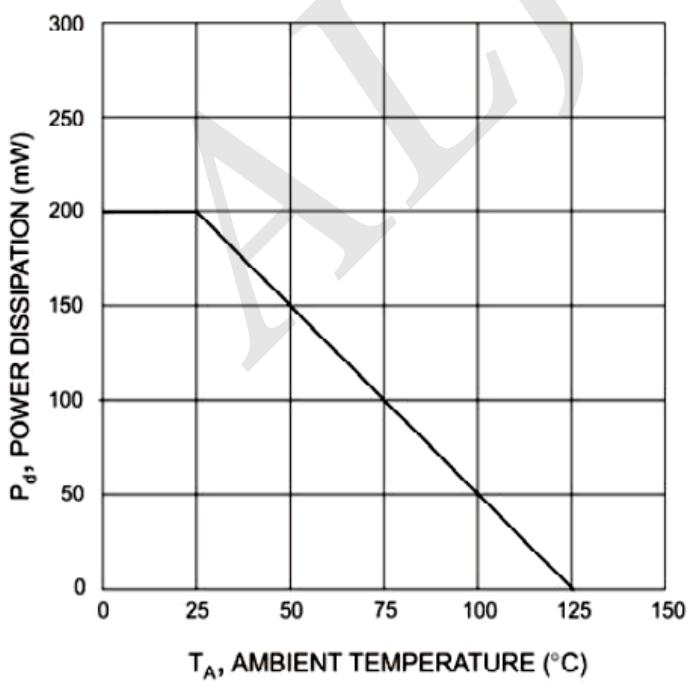


Fig. 4 Power Derating Curve